IRS2153(1)D and IR2153(1)/IR2153(1)D Comparison

About this document

Scope and purpose

The scope of this application note is to compare and highlight the differences between the IR2153(1)/IR2153(1)D and the new IRS2153(1)D high voltage, high speed power MOSFET and IGBT drivers, focusing on their electrical characteristic differences and pin-to-pin compatibility. The purpose of this document is to provide guidance to designers and engineers on how to seamlessly transition from using the IR2153(1)/IR2153(1)D to the newer IRS2153(1)D.

Intended audience

The intended audiences for this document are design engineers, technicians, and developers of electronic systems.

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1 Introduction

The new IRS2153(1)D replaces the existing IR2153(1)/IR2153(1)D HVICs advantageously by saving the need for an external bootstrap diode. It is based on the same core design and is pin-to-pin compatible, allowing minimum changes to the previous design. This application note describes the differences between the existing IR2153(1)/IR2153(1)D IC family and the new IRS2153(1)D.

2 Block Diagrams

The IR2153(1)/IR2153(1)D is not a single IC, but consists of a family of ICs (Table 1).

Table 1

P/N	Deadtime (typ.)	Internal Bootstrap Diode	Package Type
IR2153PbF	1.2 µs	No	DIP8
IR2153SPbF	1.2 µs	No	SOIC8
IR21531PbF	0.6 µs	No	DIP8
IR21531SPbF	0.6 µs	No	SOIC8
IR2153DPbF	1.2 µs	Yes	DIP8
IR2153DSPbF	1.2 µs	Yes	SOIC8
IR21531DPbF	0.6 µs	Yes	DIP8
IR21531DSPbF	0.6 µs	Yes	SOIC8

The functional block diagrams of each IC (Figs. 1 and 2) are exactly the same except the internal bootstrap diode.

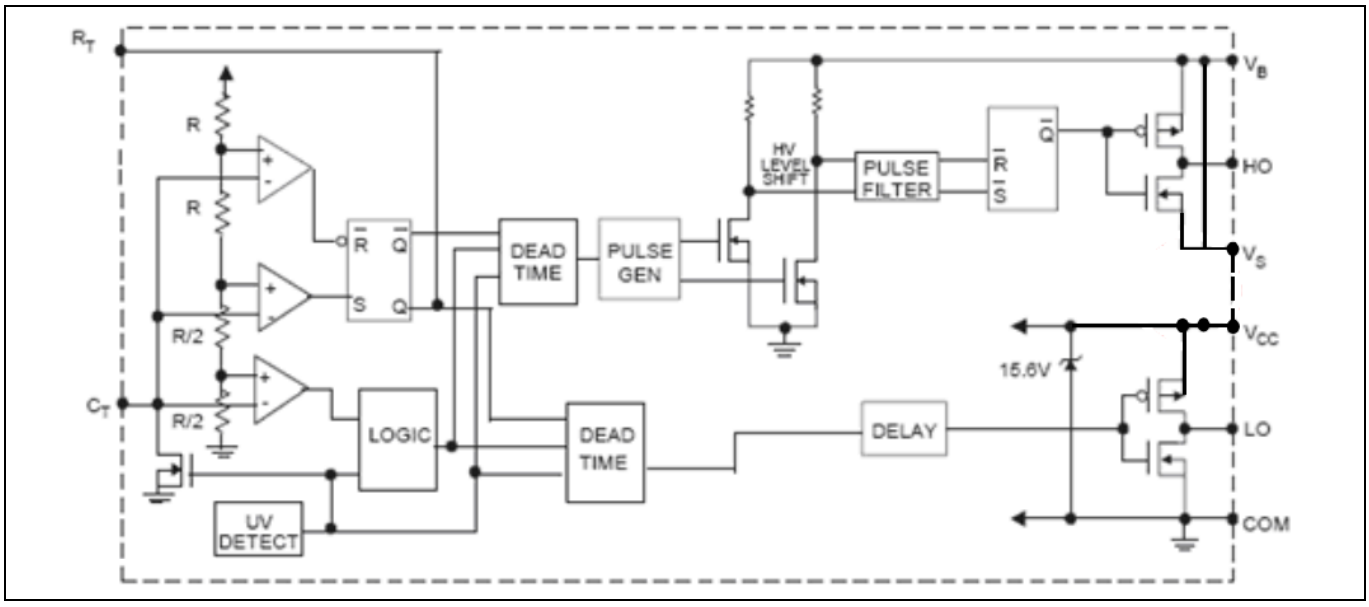

Figure 1 IR2153(1) Functional Block Diagram

Block Diagrams

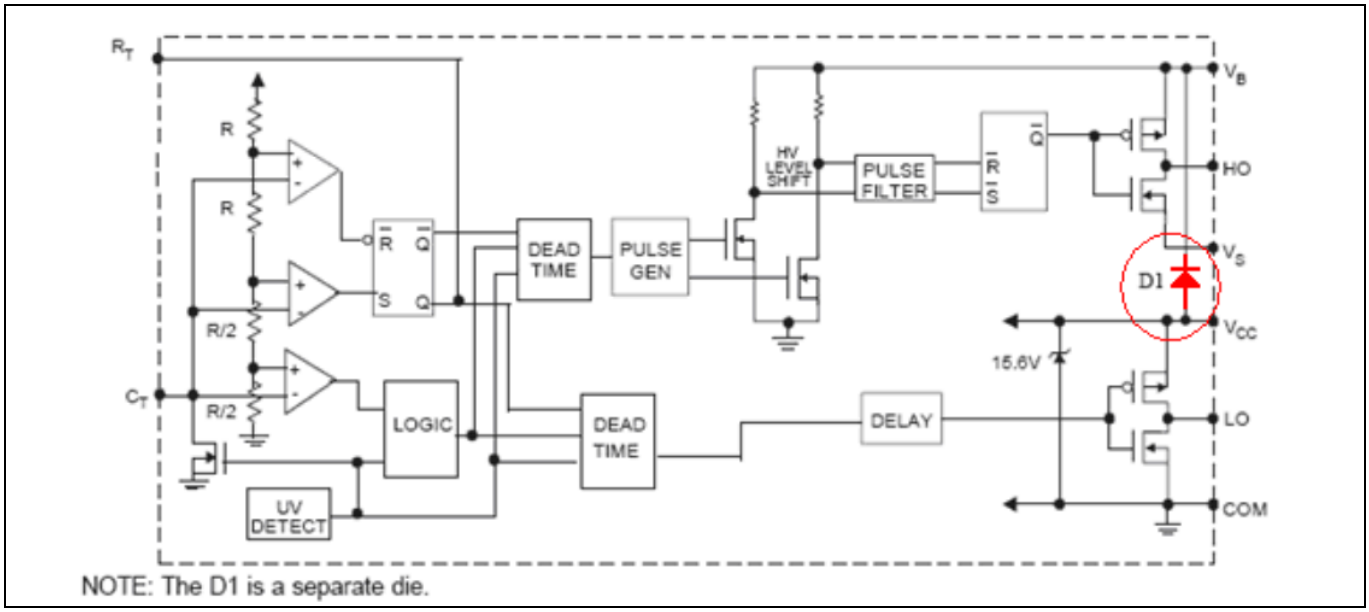

Figure 2 IR2153(1)D Functional Block Diagram

In the new IRS2153(1)D IC (Fig. 3), an internal FET now replaces the internal bootstrap diode, which was previously a separate die. IRS2153(1)D has the same functionality as IR2153(1)D and the need for an additional diode has been eliminated.

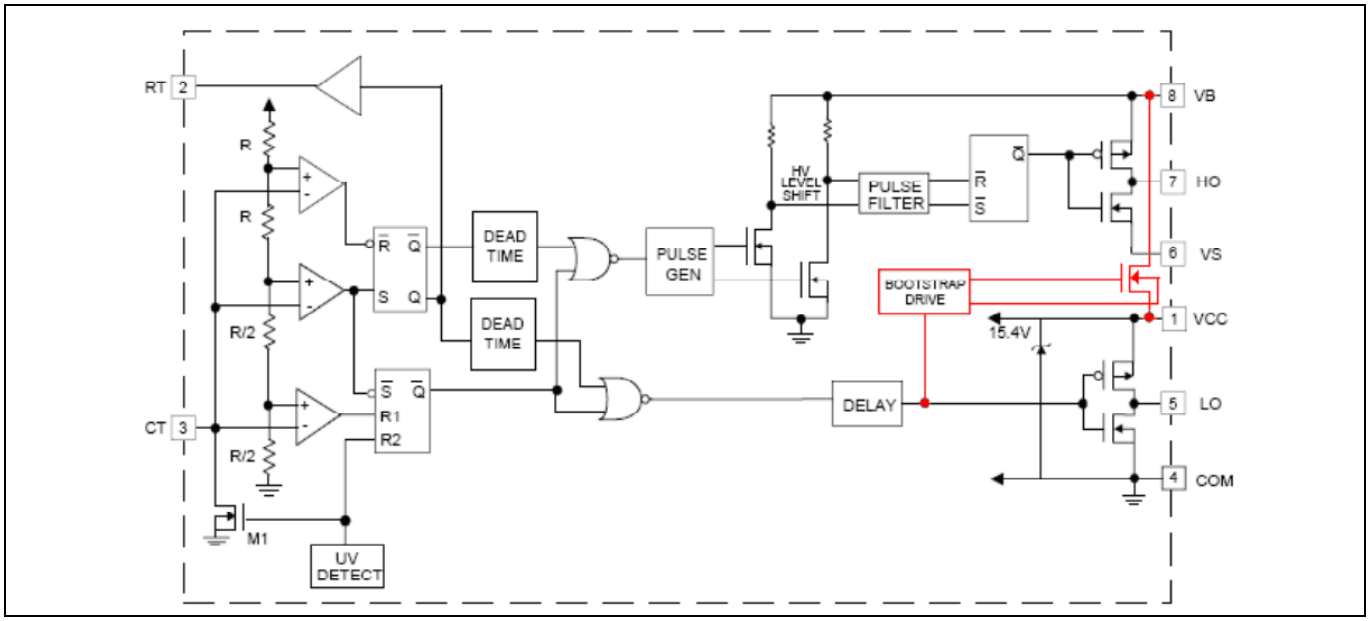

Figure 3 IRS2153(1)D Functional Block Diagram

Consequently: a customer using IR2153(1)/IR2153(1)D should take particular care of the bootstrap circuitry when switching to IRS2153(1)D.

3 IR2153(1)/IR2153(1)D vs. IRS2153(1)D Electrical Characteristics Differences

The following tables and comments highlight the differences between the IR2153(1)/IR2153(1)D and the new IRS2153(1)D:

Table 2 Absolute Maximum Ratings

Parameter		IR2153(1)/IR2153(1)D		IRS2153(1)D		Units
Symbol	**Definition**	**min**	**max**	**min**	**max**	
V_B	High side floating supply voltage	-0.3	625	-0.3	625	V
V_S	High side floating supply offset voltage	V_B – 25	V_B + 0.3	V_B – 25	V_B + 0.3	
V_{HO}	High side floating output voltage	V_S – 0.3	V_B + 0.3	V_S – 0.3	V_B + 0.3	
V_{LO}	Low side output voltage	-0.3	V_{CC} + 0.3	-0.3	V_{CC} + 0.3	
I_{RT}	RT pin current	-5	-5	-5	-5	mA
V_{RT}	RT pin voltage	-0.3	V_{CC} + 0.3	-0.3	V_{CC} + 0.3	V
V_{CT}	CT pin voltage	-0.3	V_{CC} + 0.3	-0.3	V_{CC} + 0.3	
I_{CC}	Supply current (Note 1)	-	25	-	20	mA
IO_{MAX}	Maximum allowable current at LO and HO due to external power transistor Miller effect			-500	500	
dV_S/dt	Allowable offset voltage slew rate	-50	50	-50	50	V/ns
P_D	Max. power dissipation @ $T_A \leq$ +25 °C, 8-Pin DIP	-	1.0	-	1.0	W
P_D	Max. power dissipation @ $T_A \leq$ +25 °C, 8-Pin SOIC	-	0.625	-	0.625	
R_{thJA}	Thermal resistance, junction to ambient, 8-Pin DIP	-	125	-	85	°C/W
R_{thJA}	Thermal resistance, junction to ambient, 8-Pin SOIC	-	200	-	128	
T_J	Junction temperature	-55	150	-55	150	°C
T_S	Storage temperature	-55	150	-55	150	
T_L	Lead temperature (soldering, 10 seconds)	-	300	-	300	

Comments: All absolute maximum ratings are exactly the same except for the maximum supply current limit and the thermal resistance. The maximum supply current is rated at 20 mA for the new IRS2153(1)D versus 25 mA for the IR2153(1)/IR2153(1)D and is due to the internal zener clamp. A 20 mA maximum versus 25 mA should be a negligible amount for most applications. A lower thermal resistance will give lower temperatures on the package surface.

IR2153(1)/IR2153(1)D vs. IRS2153(1)D Electrical Characteristics Differences

Table 3 Recommended Operating Conditions

Parameter		IR2153(1)/IR2153(1)D		IRS2153(1)D		Units
Symbol	**Definition**	**min**	**max**	**min**	**max**	
V_{BS}	High side floating supply voltage	V_{CC} - 0.7	V_{CLAMP}	V_{CC} - 0.7	V_{CLAMP}	V
V_S	Steady state high side floating supply offset voltage	-3.0	600	-3.0	600	
V_{CC}	Supply voltage	10	V_{CLAMP}	V_{CCUV+} + 0.1V	V_{CLAMP}	
I_{CC}	Supply current		5		5	mA
T_J	Junction temperature	-40	125	-40	125	°C

Comments: All parameters are mostly the same.

Table 4 Recommended Component Values

Parameter		IR2153(1)/IR2153(1)D		IRS2153(1)D		Units
Symbol	**Definition**	**min**	**max**	**min**	**max**	
R_T	Timing resistor value	1	-	1	-	kΩ
C_T	C_T pin capacitor value	330	-	330	-	pF

Comments: All parameters are mostly the same.

Table 5 Electrical Characteristics

Bootstrap FET/Diode Characteristics		IR2153(1)/IR2153(1)D			IRS2153(1)D			Units	Test Conditions
Symbol	**Definition**	**min**	**typ**	**max**	**min**	**typ**	**max**		
V_F	Bootstrap diode forward voltage (IR2153(1)D)	0.5	-	1.0				V	I_F = 250 mA
V_{B_ON}	V_B when the bootstrap FET is on				-	13.7	-		
I_{B_CAP}	V_B source current when bootstrap FET is on				40	55	-	mA	C_{BS}=0.1 µF
I_{B_10V}	V_B source current when bootstrap FET is on				10	12			V_B=10 V

Comments: The IRS2153(1)D contains an integrated bootstrap MOSFET that eliminates the need for an external high-voltage bootstrap diode. The integrated bootstrap MOSFET is turned on only during the time when LO is 'high' and has a limited source current due to R_{DSon}. The VBS voltage will determine each cycle by on the on-time of LO, the size of the external MOSFETs and the value of the C_{BS} capacitor. At start-up, several cycles of LO will occur first until V_{BS} increases above V_{BSUV+} (see Floating Supply Characteristics) and then HO will start to oscillate. The maximum oper¬ating frequency will be determined by the MOSFET driven by IRS2153(1)D and the value of the C_{BS} capacitor since the bootstrap MOSFET needs to maintain V_{BS} above V_{BSUV-} each cycle. If the frequency is too high, V_{BS} will fall below V_{BSUV-} and the H_O output will turn off. To avoid this problem, an external high-voltage bootstrap diode can be added in parallel to maintain V_{BS} above V_{BSUV-} during high-frequency applications.

IR2153(1)/IR2153(1)D vs. IRS2153(1)D Electrical Characteristics Differences

Table 6

Low Voltage Supply Characteristics		IR2153(1)/IR2153(1)D			IRS2153(1)D			Units	Test Conditions
Symbol	**Definition**	**min**	**typ**	**max**	**min**	**typ**	**max**		
V_{CCUV+}	Rising V_{CC} undervoltage lockout threshold	8.1	9.0	8.1	10.0	11.0	12.0	V	
V_{CCUV-}	Falling V_{CC} undervoltage lockout threshold	7.2	8.0	7.2	8.0	9.0	10.0		
$V_{CCUVHYS}$	V_{CC} undervoltage lockout hysteresis	0.5	1.0	0.5	1.6	2.0	2.4		
I_{QCCUV}	Micropower startup V_{CC} supply current	-	75	150	-	130	170	µA	$V_{CC} \le V_{CCUV-}$
I_{QCC}	Quiescent V_{CC} supply current	-	500	950	-	800	1000		
I_{CC}	V_{CC} supply current				-	1.8	-	mA	R_T=36.9 kΩ
V_{CLAMP}	V_{CC} zener clamp voltage	14.4	15.6	16.8	14.4	15.4	16.8	V	I_{CC} = 5 mA

Comments: No major changes other than V_{CCUV+} and V_{CCUV-} being higher, as well as the hysteresis. The higher UVLO thresholds should not impact the application since typically V_{CC} is regulated against its internal 15.4 V clamp voltage. The increased hysteresis should make the application more robust and prevent the IC from turning off momentarily should transient dips in the V_{CC} voltage occur.

Table 7

Low Voltage Supply Characteristics		IR2153(1)/IR2153(1)D			IRS2153(1)D			Units	Test Conditions
Symbol	**Definition**	**min**	**typ**	**max**	**min**	**typ**	**max**		
I_{QBS}	Quiescent V_{BS} supply current	-	30	50	-	60	80	µA	
V_{BSUV+}	V_{BS} supply undervoltage positive going threshold				8.0	9.0	9.5	V	
V_{BSUV-}	V_{BS} supply undervoltage negative going threshold				7.0	8.0	9.0		
I_{QBSUV-}	Micropower startup V_{BS} supply current	-	0	10				µA	$V_{CC} \le V_{CCUV-}$, $V_{CC} = V_{BS}$
V_{BSMIN}	Minimum required V_{BS} voltage for proper functionality from R_T to H_O	-	4.0	5.0				V	$V_{CC} = V_{CCUV-}$ + 0.1 V
I_{LK}	Offset supply leakage current	-	-	50	-	-	50	µA	$V_B = V_S$ = 600 V

Comments: The new IRS2153(1)D contains an under-voltage lockout circuit. This is necessary because of the additional integrated bootstrap MOSFET. The UVLO circuit will guarantee that V_{BS} is high enough before turning on H_O and will protect the external MOSFET from being driven in the linear region should V_{BS} decrease too much.

IR2153(1)/IR2153(1)D vs. IRS2153(1)D Electrical Characteristics Differences

Table 8

Low Voltage Supply Characteristics		IR2153(1)/IR2153(1)D			IRS2153(1)D			Units	Test Conditions
Symbol	**Definition**	**min**	**typ**	**max**	**min**	**typ**	**max**		
f_{OSC}	Oscillator frequency	19.4	20	20.6	18.4	19.0	19.6	kHz	R_T= 36.9/36.5 kΩ
		94	100	106	88	93	100		R_T= 7.43/7.15 kΩ
d	R_T pin duty cycle	48	50	52	-	50	-	%	f_o < 100 kHz
I_{CT}	C_T pin current	-	0.001	1.0	-	0.02	1.0	µA	
I_{CTUV}	UV-mode C_T pin pulldown current	0.30	0.70	1.2	0.2	0.3	0.6	mA	V_{CC} = 7 V
V_{CT+}	Upper C_T ramp voltage threshold	-	8.0	-	-	9.32	-	V	
V_{CT-}	Lower C_T ramp voltage threshold	-	4.0	-	-	4.66	-		
V_{CTSD}	C_T voltage shutdown threshold	1.8	2.1	2.4	2.2	2.3	2.4		
V_{RT+}	High-level R_T output voltage, V_{CC} - V_{RT}	-	10	50	-	10	50	mV	I_{RT} = -100 µA
		-	100	300	-	100	300		I_{RT} = -1 mA
V_{RT-}	Low-level R_T output voltage	-	10	50	-	10	50		I_{RT} = 100 µA
		-	100	300	-	100	300		I_{RT} = 1 mA
V_{RTUV}	UV-mode R_T output voltage	-	0	100	-	0	100		$V_{CC} \le V_{CCUV-}$
V_{RTSD}	SD-mode R_T output voltage, V_{CC} - V_{RT}	-	10	50	-	10	50		I_{RT} = -100 µA, V_{CT} = 0 V
		-	100	300	-	100	300		I_{RT} = -1 mA, V_{CT} = 0 V

Comments: The new IRS2153(1)D should fit into an existing design and maintain existing performance without any changes to the design with the exception of R_T/C_T value.

IR2153(1)/IR2153(1)D vs. IRS2153(1)D Electrical Characteristics Differences

Table 9

Low Voltage Supply Characteristics			IR2153(1)/IR2153(1)D			IRS2153(1)D			Units	Test Conditions
Symbol	**Definition**		**min**	**typ**	**max**	**min**	**typ**	**max**		
V_{OH}	High level output voltage		-	0	100	-	VCC	-	mV	I_O = 0 A
V_{OL}	Low level output voltage, V_O		-	0	100	-	COM	-		I_O = 0 A
V_{OL_UV}	UV-mode output voltage, V_O		-	0	100	-	COM	-		I_O = 0 A, $V_{CC} \le V_{CCUV-}$
t_r	Output rise time		-	80	150	-	120	220	ns	
t_f	Output fall time		-	45	100	-	50	80		
t_{sd}	Shutdown propagation delay		-	660	-	-	350	-		
t_d	Output deadtime (H_O or L_O)	2153D	0.75	1.20	1.65		1.10	1.75	µs	
		21531D	0.35	0.6	0.85		0.6	0.85		
I_{O+}	Output source current					-	180	-	mA	
I_{O+}	Output sink current					-	260	-		

Comments: Output rise and fall times are slightly longer due to a slight decrease in the output source and sink currents. Deadtime tolerances had to be slightly downgraded but should not impact most applications.

4 Conclusions

In most cases, any member for the IR2153(1)/IR2153(1)D family will be easily and advantageously replaced by the new leadfree IRS2153(1)D. The application will benefit a monolithic solution integrating a bootstrap FET, an increased UVLO hysteresis, a possibility of non-latch IC shutdown, better thermal behavior and ROHS compatibility while keeping a 3% tolerance on the frequency.

References

[1] IRS2153(1)D datasheet: https://www.infineon.com/dgdl/Infineon-IRS2153D-DataSheet-v01_00-EN.pdf?fileId=5546d46269e1c019016a4ea5480f0d88

[2] IR2153(D) datasheet: https://www.infineon.com/dgdl/Infineon-IR2153-DataSheet-v01_00-EN.pdf?fileId=5546d462533600a4015355c8c5fc16af

[3] IR21531(D) datasheet: https://www.infineon.com/dgdl/Infineon-IR21531-DataSheet-v03_00-EN.pdf?fileId=5546d462533600a4015355c8d26316b3

[4] Infineon gate driver reference page: https://www.infineon.com/cms/en/product/power/gate-driver-ics/

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Do you have a question about this document?

Email: erratum@infineon.com

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